

PNP Silicon Low Power Transistor

Rev. V3

Features

- Available in JAN, JANTX, JANTXV per MIL-PRF-19500/350
- TO-5 Package: 2N3867, 2N3868
- TO-39 Package: 2N3867S, 2N3868S
- Designed for High Speed Switching and Amplifier Applications



Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Base Breakdown Voltage	V _{CB} = -40V 2N3867, 2N3867S V _{CB} = -60V 2N3868, 2N3868S		μA dc		-100
Collector - Emitter Breakdown Voltage	I_C = -20 mA dc, 2N3867, 2N3867S I_C = -20 mA dc, 2N3868, 2N3868S	V _{(BR)CEO}	V dc	-40 -60	_
Collector - Emitter Cutoff Current	V_{EB} = +2.0 V dc, V_{CE} = -40 Vdc, 2N3867, 2N3867S V_{EB} = +2.0 V dc, V_{CE} = -60 Vdc, 2N3868, 2N3868S		μA dc	_	-1.0 -1.0
Emitter - Base Cutoff Current	V _{EB} = -4.0 Vdc	I _{EBO1}	μA dc	_	-100
Forward Current Transfer Ratio	$V_{\text{CE}} = -1.0 \text{ V dc, } I_{\text{C}} = -500 \text{ mA dc} \\ 2N3867, 2N3867S \\ 2N3868, 2N3868S \\ V_{\text{CE}} = -2.0 \text{ V dc, } I_{\text{C}} = -1.5 \text{ A dc} \\ 2N3867, 2N3867S \\ 2N3868, 2N3868S \\ V_{\text{CE}} = -3.0 \text{ V dc, } I_{\text{C}} = -2.5 \text{ A dc} \\ 2N3867, 2N3867S \\ 2N3867, 2N3867S \\ 2N3868, 2N3868S \\ V_{\text{CE}} = -5.0 \text{ V dc, } I_{\text{C}} = -3.0 \text{ mA dc} \\ \text{All Types}$	h _{FE}	-	50 35 40 30 25 20	200 150 —
Collector - Emitter Saturation Voltage	I_C = -500 mA dc, I_B = -50 mA dc I_C = -1.5 A dc, I_B = -150 mA dc I_C = -2.5 A dc, I_B = -250 mA dc	V _{CE(sat)1} V _{CE(sat)2} V _{CE(sat)3}	V dc	_	-0.5 -0.75 -1.5
Base - Emitter Saturation Voltage	I_C = -500 mA dc, I_B = -50 mA dc I_C = -1.5 A dc, I_B = -150 mA dc I_C = -2.5 A, I_B = -250 mA dc	V _{BE(sat)1} V _{BE(sat)2} V _{BE(sat)3}	V dc	-0.9	-1.0 -1.4 -2.0

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Electrical Characteristics (T_A = +25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
		_			
Collector - Emitter Cutoff Current	$T_A = +150^{\circ}\text{C}$ $V_{EB} = +2.0 \text{ V dc}, V_{CE} = -40 \text{ Vdc},$ 2N3867, 2N3867S $V_{EB} = +2.0 \text{ V dc}, V_{CE} = -60 \text{ Vdc},$ $2\text{N}3868, 2\text{N}3868\text{S}}$	I _{CEX2}	μA dc	_	-50 -50
Forward-Current Transfer Ratio	T_A = -55°C V_{CE} = -1.0 V dc, I_C = -500 mA dc 2N3867, 2N3867S 2N3868, 2N3868S		V dc	25 17	
Dynamic Characteristics					
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio	V_{CE} = -5.0 V dc, I_{C} = -100 mA dc, f = 20 MHz	h _{fe}	-	3	12
Open Circuit Output Capacitance	V _{CB} = 10 Vdc, I _E = 0, 100 kHz ≤ f ≤ 1 MHz	C _{obo}	pF	_	120
Input Capacitance	V _{CB} = -3 Vdc, I _C = 0, 100 kHz ≤ f ≤ 1 MHz	C _{ibo}	pF	_	800
Switching Characteristics					
Delay Time	V_{CC} = -30 V dc, V_{EB} = 0, I_{C} = -1.5 A dc, I_{B1} = -150 mA dc	t _d	ns	_	35
Rise Time	V_{CC} = -30 V dc, V_{EB} = 0 V dc, I_{C} = -1.5 A dc, I_{B1} = -150 mA dc	t _r	ns	_	65
Storage Time	V_{CC} = -30 V dc, V_{EB} = 0 V dc, I_{C} = -1.5 A dc, I_{B1} = I_{B2} = -150 mA dc	t _s	ns	_	500
Fall Time	V_{CC} = -30 V dc, V_{EB} = 0V dc, I_{C} = -1.5 A dc, I_{B1} = I_{B2} = -150 mA dc	t _f	ns	_	100



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Absolute Maximum Ratings (T_A = +25°C unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage 2N3867, 2N3867S 2N3868, 2N3868S	V _{CEO}	-40 V dc -60 V dc
Collector - Base Voltage 2N3867, 2N3867S 2N3868, 2N3868S	V _{CBO}	-40 V dc -60 V dc
Emitter - Base Voltage	V_{EBO}	-4.0 V dc
Collector Current	Ic	-3.0 A dc
Total Power Dissipation @ $T_A = +25^{\circ}C^{(1)}$ @ $T_C = +25^{\circ}C^{(2)}$	P _T	1.0 W 10 W
Operating & Storage Temperature Range	T _J , T _{STG}	-65°C to +200°C

⁽¹⁾ For derating, see figures 5, 6, 7 and 8 of MIL-PRF-19500/350.

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	$R_{ heta JC}$	17.5°C/W

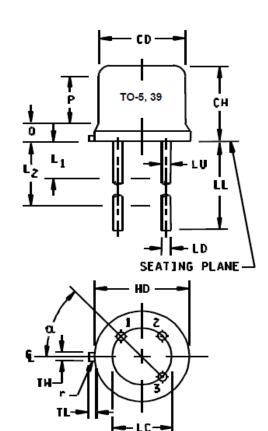
Safe Operating Area	
DC Tests:	T_C = +25°C, I Cycle, t = 1.0 s (see figure 15 of MIL-PRF-19500/350
Test 1: Test 2: Test 3:	V_{CE} = -3.33 V dc, I_{C} = -3 A dc V_{CE} = -40 V dc, I_{C} = -160 mA dc, 2N3867, 2N3867S V_{CE} = -60 V dc, I_{C} = -80 mA dc, 2N3868, 2N3868S

⁽²⁾ For thermal curves, see figures 9, 10, 11 and 12 of MIL-PRF-19500/350.

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Outline Drawings (TO-5, TO-39)

Dimensions						
Symbol	Inches Millimet		neters	Note		
	Min	Max	Min	Max		
CD	.305	.335	7.75	8.51	5, 6	
CH	.240	.260	6.10	6.60		
HD	.335	.370	8.51	9.40	4, 5	
LC	.200	TP	5.08 TP		P 7	
LD	.016	.019	0.41	0.48	8,9	
LL	See note 8, 14					
LU	.016	.019	0.41	0.48	8,9	
L ₁		.050		1.27	8,9	
L ₂	.250		6.35		8,9	
P	.100		2.54		7	
Q		.030		0.76	5	
TL	.029	.045	0.74	1.14	3,4	
TW	.028	.034	0.71	0.86	3	
r		.010		0.25	10	
α	45°	TP	45° TP		7	
1, 2, 10, 12, 13, 14						



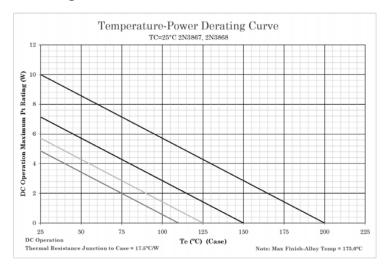
NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
- 4. Dimension TL measured from maximum HD.
- 5. Body contour optional within zone defined by HD, CD, and Q.
- 6. CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods or by gauging procedure.
- 8. Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum. Diameter is uncontrolled in and beyond LL minimum.
- 9. All three leads.
- The collector shall be internally connected to the case.
- Dimension r (radius) applies to both inside corners of tab.
- 12. In accordance with ASME Y14.5M, diameters are equivalent to \$\psi\$x symbology.
- 13. Lead 1 = emitter, lead 2 = base, lead 3 = collector.
- For non-S-suffix devices (TO-5), dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max. For S-suffix types (TO-39), dimension LL = .5 inch (12.70 mm) min. and .750 inch (19.05 mm) max.

FIGURE 1. Physical dimensions (similar to TO-5, TO-39).

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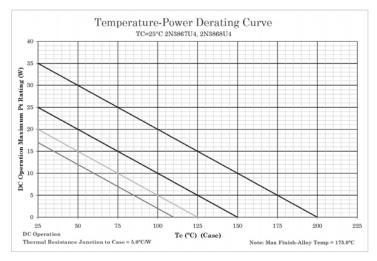
Temperature-Power Derating Curves



NOTES:

- All devices are capable of operating at ≤ T_J specified on this curve. Any parallel line to this curve will
 intersect the appropriate power for the desired maximum T_J allowed.
- 2. Derate design curve constrained by the maximum junction temperatures and power rating specified. (See
- Derate design curve chosen at $T_J \le 150^{\circ}C$, where the maximum temperature of electrical test is performed. Derate design curve chosen at $T_J \le 125^{\circ}C$, and $110^{\circ}C$ to show power rating where most users want to limit T_J in their application.

FIGURE 5. Derating for 2N3867, 2N3868 (TO-5, TO-39).



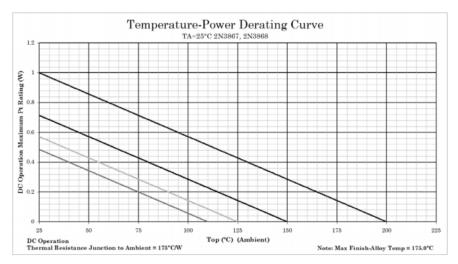
NOTES:

- All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T₁ allowed.
- Derate design curve constrained by the maximum junction temperatures and power rating specified. (See
- Derate design curve chosen at $T_J \le 150^{\circ}C$, where the maximum temperature of electrical test is performed. Derate design curve chosen at $T_J \le 125^{\circ}C$, and $110^{\circ}C$ to show power rating where most users want to limit
- T_J in their application.

FIGURE 6. Derating for 2N3867U4, 2N3868U4

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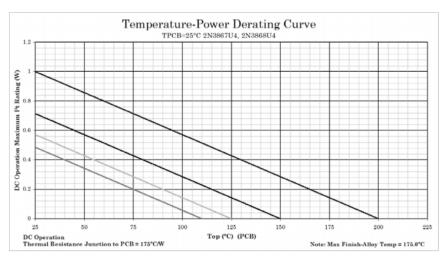
Temperature-Power Derating Curves



NOTES:

- All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
- Derate design curve constrained by the maximum junction temperatures and power rating specified. (See
- Derate design curve chosen at T_J ≤ 150°C, where the maximum temperature of electrical test is performed.
- Derate design curve chosen at T_J ≤ 125°C, and 110°C to show power rating where most users want to limit

FIGURE 7. Derating for 2N3867, 2N3868.



- 1. All devices are capable of operating at ≤ T_J specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
- Derate design curve constrained by the maximum junction temperatures and power rating specified. (See 1.3 herein.)
- Derate design curve chosen at $T_J \le 150^{\circ}C$, where the maximum temperature of electrical test is performed. Derate design curve chosen at $T_J \le 125^{\circ}C$, and $110^{\circ}C$ to show power rating where most users want to limit T_J in their application.

FIGURE 8. Derating for 2N3867U4, 2N3868U4.

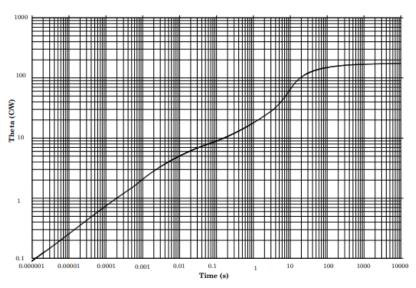


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Thermal Impedance Curves

Maximum Thermal Impedance

Free Air Ta=25C



R_{θJA} = 175 °C/W

FIGURE 9. Thermal impedance for 2N3867 and 2N3868 (TO-5 and TO-39).

Maximum Thermal Impedance

Tc=25C Time (s)

R_{eJC} = 17.5 °C/W

FIGURE 10. Thermal impedance for 2N3867 and 2N3868 (TO-5 and TO-39).

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Thermal Impedance Curves

Maximum Thermal Impedance

Solder mounted to copper heatsink at Tc=25C

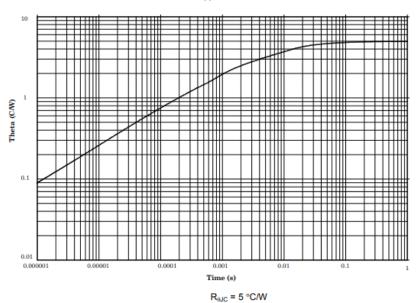


FIGURE 11. Thermal impedance for 2N3867U4, 2N3868U4.

Maximum Thermal Impedance

Solder mounted to FR4 PCB with minimal copper content.

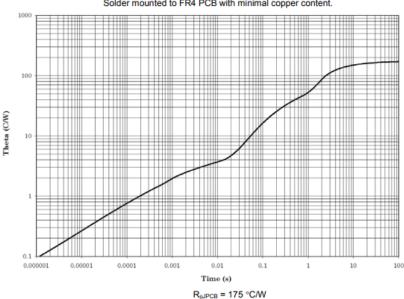


FIGURE 12. Thermal impedance for 2N3867U4, 2N3868U4.



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